Hopping conduction in strongly insulating states of a bent quantum Hall junction

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Transport studies of a bent quantum Hall junction at integer filling factor ν show strongly insulating states ($\nu = 1,2$) at higher fields. In this paper we analyze the strongly insulating behavior as a function of temperature T and dc bias V_{dc} , in order to classify the localization mechanisms responsible for the insulating state. The temperature dependence suggests a crossover from activated nearest-neighbor hopping at higher T to variable-range hopping conduction at lower T $(G \sim \exp(-(\frac{T_0}{T})^{1/2}))$. The base temperature electric field dependence shows $I(\mathcal{E}) \sim \exp(-(\frac{\mathcal{E}_0}{\mathcal{E}})^{1/2})$, consistent with 1D variable-range hopping conduction. We observe almost identical behavior at $\nu = 1$ and $\nu = 2$, indicating that the bent quantum Hall junction conductance is independent of the bulk spin polarization. Various models of 1D variable range hopping which either include or ignore interactions are compared, all of which are consistent with the basic model of disorder coupled counter-propagating quantum Hall edges.

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Disorder and interactions in one-dimensional (1D) conductors can backscatter propagating charge, leading to localization of electronic states at low temperatures. Interactions could further modify the conduction characteristics [1, 2, 3] and lead to a temperature-dependent localization transition [4, 5]. In chiral 1D systems like quantum Hall (QH) edges [6, 7] charge propagates in only one direction, but with counter-propagating chiral quantum Hall edge states coupled along an extended junction [8, 9, 10], a nonchiral interacting 1D system can form at such a QH line junction [11, 12, 13, 14, 15, 16], and reveal information about generic 1D systems.

In this work we study a line junction of integer quantum Hall edges in a 90° bent QH (BQH) junction. Previous work introduced the corner overgrowth technique for fabricating bent two-dimensional electron systems (2DES) and demonstrated the propagation of quantum Hall edge channels along the 90° junction [9]. At equal filling factors ν on both facets of the bent quantum Hall system, an equal number of edge channels propagates along the junction in both directions, forming a non-chiral system of strongly coupled edge states. Conductance measurements of the bent quantum Hall junction show evidence for two different phases in the integer quantum Hall regime, depending on the filling factor ν : A strongly insulating phase at $\nu = 1$ and $\nu = 2$ and a weakly insulating phase at $\nu > 2$ [10]. This paper concerns itself with classifying the localization mechanisms that lead to an insulating state at the lowest Landau level filling factors.

The investigated sample structure is a high-mobility two-dimensional electron system bent at a 90° angle, fabricated using corner overgrowth [9]. A modulation doped AlGaAs/GaAs heterointerface structure is overgrown on an ex-situ cleaved GaAs (110) corner substrate, where a bent 2DES forms at the interface between the GaAs base layer and the AlGaAs barrier. The exact layer sequence is described in Ref. [9]. Indium contacts alloyed along the edges of both facets of the sample provide ohmic contacts to the bent 2D system. After illu-



FIG. 1: Small signal conductance $G = dI/dV|_{V=0}$ of the bent quantum Hall junction vs. filling factor ν and temperature. The inset illustrates the flow of edge currents in the bent quantum Hall system, for the case of equal ν on the two facets. The current flowing along the bent quantum Hall junction is proportional to the cross-corner voltage drops V_{cc} or V'_{cc} , respectively. With the voltage V_s between the edge channels incident to the junction, the conductance G along the junction can be calculated. The gray scale indicates temperature increments by $\times 2$.

mination with red light at T = 4.2 K we obtain electron sheet densities of $n_{(110)} = 1.11 \cdot 10^{11} \,\mathrm{cm}^{-2}$ on the (110)-facet and $n_{(1\bar{1}0)} = 1.41 \cdot 10^{11} \,\mathrm{cm}^{-2}$ on the (1 $\bar{1}0$)-

facet. The estimated electron mobility on both facets is $\mu = 0.5 \cdot 10^6 \text{ cm}^2/\text{Vs}$. We measure the conductance of the bent quantum Hall junction, where a tilted magnetic field *B* is applied at a tilt angle such that both facets form quantum Hall systems with equal filling factors. The inset in Fig. 1 illustrates the resulting flow of edge currents and the schematic contact configuration for the bent quantum Hall sample. At equal filling factors ν on both facets, according to the Landauer-Buttiker formalism the current *I* flowing along the BQH junction is proportional to the voltage drop V_{cc} or V'_{cc} (Fig. 1, inset) across the junction: $I = \nu \frac{e^2}{h} V_{cc}$. The conductance *G* is then calculated dividing the measured current *I* by the supplied voltage V_s [11, 13]:

$$G = \nu \frac{e^2}{h} \frac{V_{cc}}{V_s} = \nu \frac{e^2}{h} \frac{V_{cc}'}{V_s} \tag{1}$$

This conductance equation is only valid within magnetic field intervals where the facets are in the QH regime, $R_{xx} = 0$, and no current is scattered away from the junction. This is ensured by measuring the second cross-corner voltage V'_{cc} (see Fig. 1, inset), which equals V_{cc} only if no current leaks across the facet. Fig. 1 shows a plot of the BQH junction conductance measured at various filling factors ν and at fixed temperatures between 30 mK and 2.0 K. The two curves shown for each temperature correspond to the conductance deduced from a measurement of V_{cc} and V'_{cc} .

The conductance vanishes at the base temperature T = 30 mK, and rises strongly with increasing T. Phenomenologically we describe the behavior at $\nu = 1, 2$ as strongly insulating. To measure the temperature dependence of the conductance, the magnetic field is set at $\nu = 1$ or $\nu = 2$, respectively, while the conductance along the BQH junction is measured in a continuous temperature sweep. Fig. 2 a) shows a double-logarithmic plot of the zero bias conductance $G = dI/dV|_{V=0}$ vs. temperature T measured with a 10 nA AC excitation. As the temperature is decreased by roughly one order of magnitude, the conductance G in Fig. 2 a) drops by two orders of magnitude, where no single exponent is able to characterize the full temperature range. Note the different noise level in the $\nu = 1$ and $\nu = 2$ data, which is due to the quantized conductance of the quantum Hall edges contacting the BQH junction. The current along the junction is measured as the current difference between the edge channels of the two facets. At $\nu = 2$ the conductance of the edge channels is twice as high as for $\nu = 1$. This means that for the same current I the voltage V_{cc} measured at $\nu = 2$ is only half the value measured at $\nu = 1$. We multiply by the filling factor in Eq. 1 and obtain the same conductance value as for $\nu = 1$, but with a higher noise level.

We observe almost identical behavior at $\nu = 1$ and $\nu = 2$, although the bulk $\nu = 2$ state corresponds to a fully occupied, spin-degenerate lowest Landau level, while in the bulk $\nu = 1$ state the spin degeneracy is lifted. This spin-independent conductance is also ob-



FIG. 2: a) Small signal conductance $G = dI/dV|_{V=0}$ at filling factors $\nu = 1, 2$, plotted on a double-log scale vs. temperature T. We observe a very low conductance with strong temperature dependence. Panel b) shows an Arrhenius plot of the conductance G at $\nu = 1$ and $\nu = 2$. In panel c) the same data is plotted semi-logarithmically vs. $T^{-\frac{1}{2}}$. The low temperature behavior (below ≈ 320 mK) fits an exponential in $T^{-\frac{1}{2}}$, consistent with one-dimensional VRH conduction [18, 19]. At higher temperature the conductance seems exponential in (1/T), indicating activated behavior.

served at filling factors 3,4 and 5,6 [10]. A possible

explanation could be that the sharp edge potential of the corner-overgrown system prohibits the formation of incompressible strips and the spatial separation of the spin-split edges [20]. Also Kim and Fradkin [14] predicted a qualitatively similar behavior for a system of counterpropagating $\nu = 1$ and $\nu = 2$ edges coupled through a single impurity.

To investigate whether there is evidence of hopping conduction, the data from Fig. 2(a) is plotted semilogarithmically vs. T^{-1} in Fig. 2(b). The high temperature data above $\sim~320$ mK is fitted to an activated temperature dependence $G \sim \exp(-(\frac{\Delta}{k_B T}))$, with $\Delta = 87.3 \,\mu\text{eV}$ at $\nu = 1$ and $\Delta = 89.0 \,\mu\text{eV}$ at $\nu = 2$. To check for variable range hopping conduction, the same data is plotted in Fig. 2(c) vs. $T^{-1/2}$. At temperatures below ~ 320 mK the conductance can be described by variable-range hopping conduction of the form $G(T) \sim \exp(-(\frac{T_0}{T})^{1/2})$ with $T_0 = 11.0$ K at $\nu = 1$. The data at $\nu = 2$ is consistent with $\nu = 1$, yet the higher noise level does not allow for an independent fit. These observations indicate crossover from thermally activated nearest-neighbor hopping conduction at higher temperatures to one-dimensional VRH conduction at lower T[17, 18, 19].

Since the characteristics of VRH conduction should also become evident in the electric field dependence of the conductance, we measure the differential conductance along the BQH junction as a function of an applied dc bias. For these measurements we apply a dc bias voltage modulated with an ac signal of 20 μ V to the V_s contacts sketched in Fig. 1. The ac current along the junction was again measured by the cross corner voltages V_{cc} and V'_{cc} with a known R_{xy} facet impedance. Fig. 3 a) shows a double-logarithmic plot of the I(V) curves at $\nu = 1, 2$ obtained by integrating the differential conductance over V_{dc} . Compared to the temperature dependence shown in Fig. 2, the I(V) curves of Fig. 3 show a similarly strong dependence on V_{dc} , where I drops by roughly two orders of magnitude as V_{dc} is decreased by one order of magnitude. $\nu = 1$ could not be measured for the complete voltage range, since current leakage across the facet became evident at higher voltages $V_{cc} \neq V_{cc'}$.

To analyze the possible conductance mechanism, in Fig. 3 we compare semi-logarithmic plots of the current I (panel b)) and the conductance $G = I/V_{dc}$ (panel c)) vs. the inverse square root of the dc electric field \mathcal{E} . The electric field was obtained by assuming a uniform \mathcal{E} along the junction and dividing the dc bias V_{dc} by the junction length of 4 mm. Nattermann, Malinin *et al.* [3] predict one-dimensional variable-range hopping with an exponential dependence $I(\mathcal{E}) \sim \exp(-(\mathcal{E}_0/\mathcal{E})^{1/2})$ for electric fields \mathcal{E} larger than the crossover field associated with the localization length. For $\nu = 1$ ($\nu = 2$), a fit with $\mathcal{E}_0 = 68.1$ V/m (46.0 V/m) describes the $I(\mathcal{E})$ dependence in the electric field range above $\mathcal{E}^{-1/2} = 1.0$ V/m ($\mathcal{E}^{-1/2} = 1.25$ V/m) quite well (Fig. 3 b)). Fogler and Kelly [2] point out that Refs. [3] do not correctly account for highly resistive segments in the con-



FIG. 3: (a) The I(V) curves at base temperature T = 30 mK, plotted on a double-log scale. (b) The current I plotted semilogarithmically vs. the inverse square root of the applied dc electric field \mathcal{E} . For $\nu = 1$ ($\nu = 2$), an exponential in $\mathcal{E}^{-1/2}$ describes the $I(\mathcal{E})$ dependence in the electric field range above $\mathcal{E}^{-1/2} = 1.0$ V/m ($\mathcal{E}^{-1/2} = 1.25$ V/m) quite well. (c) Large signal conductance G = I/V also versus inverse square root of \mathcal{E} . An exponential dependence $G(\mathcal{E}) \sim \exp(-(\mathcal{E}_0/\mathcal{E})^{1/2})$ fits the $\nu = 2$ data at high electric fields.

ducting path, which are unavoidable in one dimension. They predict a linear response at low fields, followed by an intermediate regime, and an exponential dependence $G(\mathcal{E}) \sim \exp(-(\mathcal{E}_0/\mathcal{E})^{1/2})$ for the conductance at high electric fields, with a typically s-shaped I(V) curve. Fig. 3 c) shows a semi-logarithmic plot of the conductance G vs. $\mathcal{E}^{-1/2}$, where only the $\nu = 2$ data at high fields above $\mathcal{E} = 2.5$ V/m the fits to an exponential behavior with $\mathcal{E}_0 = 10.1$ V/m. Our experimental data is clearly in favor of the earlier model [3], and we point out that the bent quantum Hall junction possibly represents a geometry where highly resistive breaks on the 1D conducting path can be avoided: a highly resistive impurity could locally separate the chiral quantum Hall edges, allowing the current to circumvent the break.

Considering existing theory, the insulating state could either be caused by a bandgap in the dispersion, leading to activated conduction, or by localization leading to hopping conduction. While a previous publication [10] was not able to distinguish between the two possible conduction mechanisms, the data presented here is in favor of hopping conduction. The temperature and dc bias dependence are both consistent with 1D VRH conduction at low temperatures. The temperature dependence of the BQH junction conductance at $\nu = 1, 2$ is consistent with a crossover from activated nearestneighbor hopping conduction to 1D VRH conduction $(G(T) \sim \exp(-(T_0/T)^{1/2}))$ below T = 320 mK. The measured $I(\mathcal{E})$ dependence is described best by 1D VRH conduction of the form $I \sim \exp(-(\mathcal{E}_0/\mathcal{E})^{1/2})$ [3]. The larger value for E_0 observed at $\nu = 1$ suggests a magnetic field dependent localization length, which decreases at higher fields.

Coulomb interactions between the counterpropagating integer QH edges could be responsible

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for the appearance of the strongly insulating state only at high fields [12, 14], with a strongly insulating behavior predicted for a system of tunnel coupled QH edges at $\nu = 1, 2$. An insulating state was experimentally observed in this system as a zero-bias tunneling peak at $\nu = 1, 2$ [8].

In conclusion, we performed magnetotransport studies of a bent quantum Hall junction with equal integer filling factors $\nu = 1, 2$, and observed a strongly insulating phase at high B with apparently spin-independent conduction. The temperature and electric field dependence of the conductance suggest VRH conduction as the low-temperature transport mechanism. The role of Coulomb interactions, which are possibly causing the high-field insulator in the BQH junction, could be clarified by conductance measurements over an extended temperature and voltage range in the strongly insulating regime, which should be possible in higher mobility samples, and a more detailed study of the weakly insulating phase at low B, which should be possible in gated samples.

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